

Photoluminescence and conductivity compensation effects in fast-electron irradiated InP epilayers

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Abstract

Strong interaction between residual donor impurities and radiation defects was evidenced by studying the photoluminescence spectra of bound excitons in fast-electron ($E=4$ MeV) irradiated n-InP epilayers. A diminution of the conductivity compensation degree with the dose of electron irradiation has been observed, which proves to be connected with the intensive formation of deep ($E_c-0.4$ eV) radiation donor-type defects.

References

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